WHAT IS CLAIMED IS:

1. A conductive film consisting of a silver alloy having a component composition containing 0.1 to 1.5 at% of at least one of In and Sn and further containing 0.1 to 3.5 at% of Sb with the balance composed of Ag and unavoidable impurities.

2. The conductive film according to claim 1, wherein the conductive film is a reflective electrode film for an OLED element in which a transparent conductive film for an OLED element is laminated on the surface of the conductive film and an electroluminescent layer including an organic EL layer is further laminated on the transparent conductive film.

3. The conductive film according to claim 1, wherein the conductive film is a reflective electrode film for a light-emitting diode.

4. The conductive film according to claim 1, wherein the conductive film is a wiring film for a touch panel.

5. A method for producing the conductive film according to claim 1, wherein the conductive film is formed by sputtering using a sputtering target consisting of a silver alloy having a component composition containing 0.1 to 1.5 at% of at least one of In and Sn and further

containing 0.1 to 3.5 at% of Sb with the balance composed of Ag and unavoidable impurities.

6. A sputtering target used for the method according to claim 5, wherein the sputtering target consists of a silver alloy having a component composition containing 0.1 to 1.5 at% of at least one of In and Sn and further containing 0.1 to 3.5 at% of Sb with the balance composed of Ag and unavoidable impurities.

7. The sputtering target according to claim 6, wherein the sputtering target is produced by a plastic forming process on an ingot formed by melting and casting a silver alloy.

8. The sputtering target according to claim 7, wherein the sputtering target is produced by subjecting an ingot to heat treatment after the ingot is subject to the plastic forming process.

CLAIMS

[Claim 1] A conductive film consisting of a silver alloy having a component composition containing 0.1 to 1.5 at% of at least one of In and Sn and further containing 0.1 to 3.5 at% of Sb with the balance composed of Ag and unavoidable impurities, and the conductive film is formed by sputtering using a sputtering target.

[Claim 2] The conductive film according to claim 1, wherein the conductive film is a reflective electrode film for an OLED element in which a transparent conductive film for an OLED element is laminated on the surface of the conductive film and an electroluminescent layer including an organic EL layer is further laminated on the transparent conductive film.

[Claim 3] The conductive film according to claim 1, wherein the conductive film is a reflective electrode film for a light-emitting diode.

[Claim 4] The conductive film according to claim 1, wherein the conductive film is a wiring film for a touch panel.

[Claim 5] A method for producing the conductive film according to any one of claims 1 to 4, wherein the conductive film is formed by sputtering using a sputtering target consisting of a silver alloy having a component composition containing 0.1 to 1.5 at% of at least one of In and Sn and further containing 0.1 to 3.5 at% of Sb with the balance composed of Ag and unavoidable impurities.

[Claim 6] A sputtering target used for the method according to claim 5, wherein the sputtering target consists of a silver alloy having a component composition containing 0.1 to 1.5 at% of at least one of In and Sn and further containing 0.1 to 3.5 at% of Sb with the balance composed of Ag and unavoidable impurities.

[Claim 7] The sputtering target according to claim 6, wherein the sputtering target is produced by a plastic forming process on an ingot formed by melting and casting a silver alloy.

[Claim 8] The sputtering target according to claim 7, wherein the sputtering target is produced by subjecting an ingot to heat treatment after the ingot is subject to the plastic forming process.